

DESCRIPTION

The CNX48U, H11BX, MOC8080 and TIL113 have a gallium arsenide infrared emitter optically coupled to a silicon planar photodarlington.

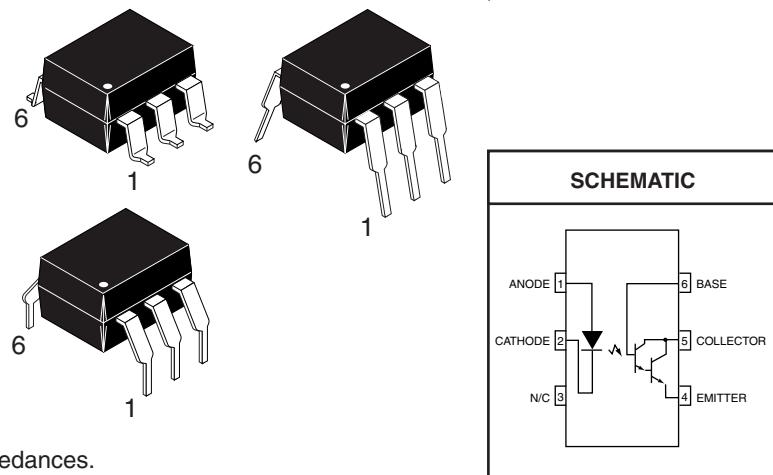
CNX48U	H11B1	H11B2	H11B255	H11B3
MOC8080	TIL113			

FEATURES

- High sensitivity to low input drive current
- Meets or exceeds all JEDEC Registered Specifications
- VDE 0884 approval available as a test option
-add option .300. (e.g., H11B1.300)

APPLICATIONS

- Low power logic circuits
- Telecommunications equipment
- Portable electronics
- Solid state relays
- Interfacing coupling systems of different potentials and impedances.



Parameter	Symbol	Device	Value	Units
TOTAL DEVICE				
Storage Temperature	T_{STG}	All	-55 to +150	°C
Operating Temperature	T_{OPR}	All	-55 to +100	°C
Lead Solder Temperature	T_{SOL}	All	260 for 10 sec	°C
Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	All	250	mW
Derate above 25°C			3.3	mW/°C
EMITTER				
Continuous Forward Current	I_F	All	100	mA
Reverse Voltage	V_R	All	6	V
Forward Current - Peak (300 μs , 2% Duty Cycle)	$I_F(\text{pk})$	All	3.0	A
LED Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	All	100	mW
Derate above 25°C			1.8	mW/°C
DETECTOR				
Collector-Emitter Breakdown Voltage	BV_{CEO}	CNX48U, TIL113 H11B1, H11B2 H11B3 H11B255 MOC8080	30 25 55	V
Collector-Base Breakdown Voltage	BV_{CBO}	CNX48U, H11B1 H11B2, H11B3 TIL113 H11B255 MOC8080	30 55	V
Emitter-Collector Breakdown Voltage	BV_{ECO}	All	7	V
Detector Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	All	150 2.0	mW mW/°C
Derate above 25°C				

CNX48U	H11B1	H11B2	H11B255	H11B3
MOC8080	TIL113			

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise specified.)

INDIVIDUAL COMPONENT CHARACTERISTICS

Parameter	Test Conditions	Symbol	Device	Min	Typ**	Max	Unit
EMITTER	($I_F = 10 \text{ mA}$)	V_F	H11B1, H11B2				V
	($I_F = 10 \text{ mA}$)		H11B255	0.8	1.2	1.5	
	($I_F = 10 \text{ mA}, T_A = -55^\circ\text{C}$)		MOC8080				
	($I_F = 10 \text{ mA}, T_A = 100^\circ\text{C}$)		TIL113				
	($I_F = 50 \text{ mA}$)		CNX48U		1.2	1.3	
Input Forward Voltage	($I_F = 10 \text{ mA}$)	V_F	MOC8080	0.9	1.3	1.7	V
	($I_F = 10 \text{ mA}, T_A = -55^\circ\text{C}$)		H11B3	0.7	1.05	1.4	
	($I_F = 10 \text{ mA}, T_A = 100^\circ\text{C}$)				1.35	1.5	
Reverse Leakage Current	($V_R = 6 \text{ V}$)	I_R	All		0.001	10	μA
Capacitance	($V_F = 0 \text{ V}, f = 1.0 \text{ MHz}$)	C	All		50		pF
DETECTOR	($I_C = 1 \text{ mA}, I_F = 0$)	BV_{CEO}	CNX48U	30	60		V
	($I_C = 100 \mu\text{A}, I_F = 0$)		TIL113				
	($I_C = 10 \text{ mA}, I_F = 0$)		H11B1, H11B2	25	60		
	($I_C = 100 \mu\text{A}, I_F = 0$)		H11B3				
	($I_C = 1 \text{ mA}, I_F = 0$)		H11B255	55	70		
Collector-Emitter Breakdown Voltage	($I_C = 100 \mu\text{A}, I_E = 0$)	BV_{CBO}	MOC8080				V
	($I_C = 100 \mu\text{A}, I_F = 0$)		CNX48U, H11B1	30	100		
	($I_C = 100 \mu\text{A}, I_E = 0$)		H11B2, H11B3				
	($I_C = 100 \mu\text{A}, I_F = 0$)		TIL113				
Collector-Base Breakdown Voltage	($I_C = 100 \mu\text{A}, I_E = 0$)	BV_{CBO}	H11B255	55	100		V
	($I_C = 100 \mu\text{A}, I_F = 0$)		MOC8080				
Emitter-Collector Breakdown Voltage	($I_E = 100 \mu\text{A}, I_B = 0$)	BV_{ECO}	All	7	10		V
Collector-Emitter Dark Current	($V_{CE} = 10 \text{ V}$, Base Open)	I_{CEO}	All		1	100	nA

Note

** Typical values at $T_A = 25^\circ\text{C}$

CNX48U	H11B1	H11B2	H11B255	H11B3
MOC8080	TIL113			

TRANSFER CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise specified.)

DC Characteristics	Test Conditions	Symbol	Device	Min	Typ**	Max	Units
Collector Output Current ⁽¹⁾	($I_F = 10 \text{ mA}$, $V_{CE} = 5 \text{ V}$)	I_C (CTR)	MOC8080	50 (500)			mA (%)
	($I_F = 10 \text{ mA}$, $V_{CE} = 1 \text{ V}$)		H11B255	10 (100)			
	($I_F = 1 \text{ mA}$, $V_{CE} = 5 \text{ V}$)		CNX48U	60 (600)			
	($I_F = 1 \text{ mA}$, $V_{CE} = 1 \text{ V}$)		TIL113	30 (300)			
	($I_F = 0.5 \text{ mA}$, $V_{CE} = 1 \text{ V}$)		H11B1	5 (500)			
			H11B2	2 (200)			
Saturation Voltage	($I_F = 1 \text{ mA}$, $I_C = 1 \text{ mA}$)	$V_{CE(\text{sat})}$	H11B1, H11B2			1.0	V
	($I_F = 5 \text{ mA}$, $I_C = 10 \text{ mA}$)		H11B3, MOC8080			1.0	
	($I_F = 50 \text{ mA}$, $I_C = 50 \text{ mA}$)		CNX48U			1.0	
	($I_F = 8 \text{ mA}$, $I_C = 2 \text{ mA}$)		H11B255			1.25	
AC Characteristics	($I_C = 10 \text{ mA}$, $V_{CE} = 10 \text{ V}$) ($R_L = 100 \Omega$) (Fig.7)	t_{on}	H11B1		25		μs
		t_{off}	H11B2		18		
	($I_F = 10 \text{ mA}$, $V_{CC} = 5 \text{ V}$) ($R_E = 100 \Omega$), ($R_{BE} = 1M\Omega$) (Fig. 8)	t_{on}	CNX48U		3.5		
		t_{off}			36		
	($I_F = 1 \text{ mA}$, $V_{CC} = 5 \text{ V}$) ($R_E = 1k\Omega$), ($R_{BE} = 10M\Omega$) (Fig. 8)	t_{on}			70		
		t_{off}			190		
	($I_F = 5 \text{ mA}$, $V_{CC} = 10 \text{ V}$) ($R_L = 100 \Omega$) (Fig.7)	t_{on}	MOC8080		3.5		
		t_{off}			25		
	($I_F = 200 \text{ mA}$, $I_C = 50 \text{ mA}$) ($V_{CC} = 10 \text{ V}$) ($R_L = 100 \Omega$) (Fig.7)	t_{on}	TIL113		0.35	5	
		t_{off}			55	100	

ISOLATION CHARACTERISTICS

Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Units
Input-Output Isolation Voltage ⁽²⁾	($I_{I-O} \leq 1 \mu\text{A}$, V_{rms} , $t = 1 \text{ min.}$)		5300			Vac(rms)
Isolation Resistance ⁽²⁾	($V_{I-O} = 500 \text{ VDC}$)	R_{ISO}		10^{11}		Ω
Isolation Capacitance ⁽²⁾	($V_{I-O} = \emptyset$, $f = 1 \text{ MHz}$)	C_{ISO}		0.8		pf

Note

** Typical values at $T_A = 25^\circ\text{C}$

CNX48U	H11B1	H11B2	H11B255	H11B3
MOC8080	TIL113			

Fig. 1 Output Current vs. Input Current

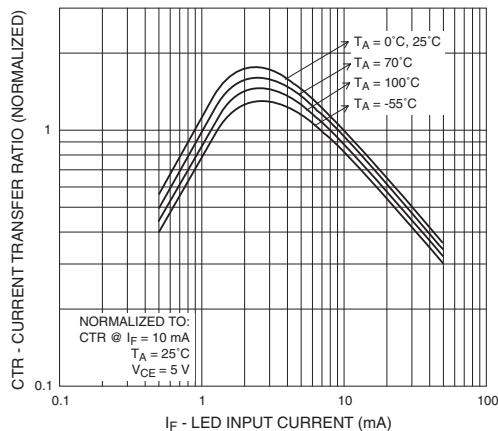


Fig. 2 Current Transfer Ratio vs. Ambient Temperature

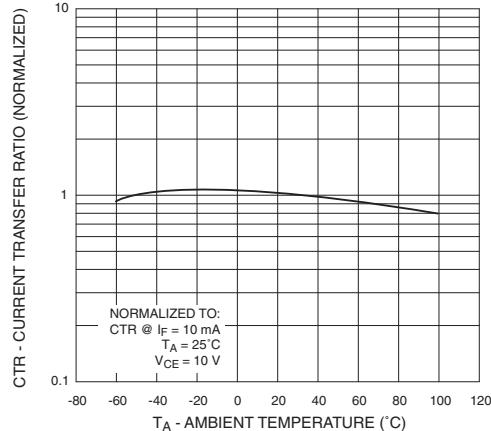


Fig. 3 Collector Current vs. Collector-Emitter Voltage

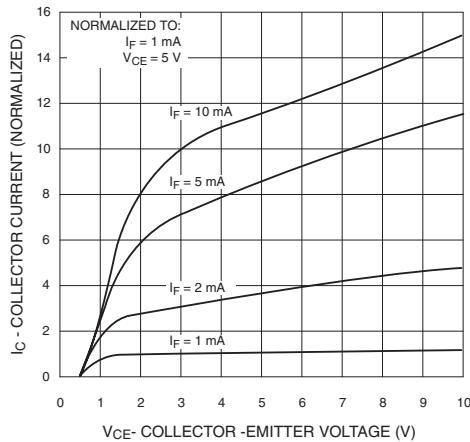


Fig. 4 Dark Current vs. Ambient Temperature

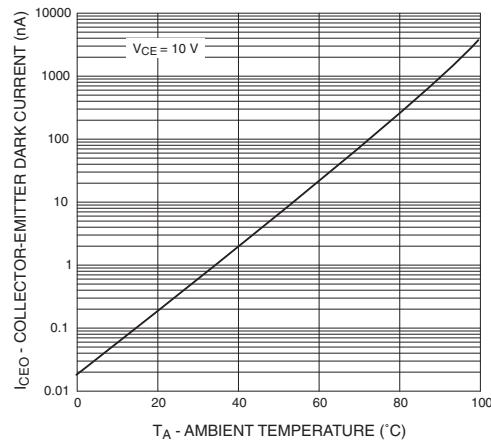


Fig. 5 Turn-On Time vs. Input Current

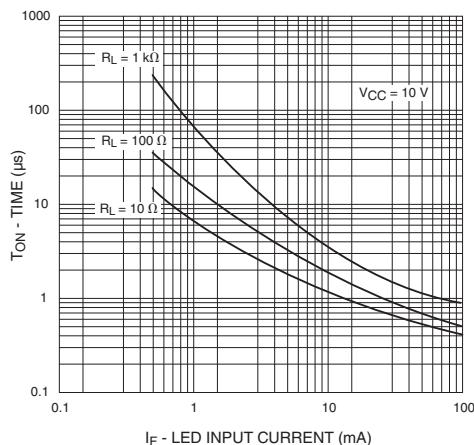
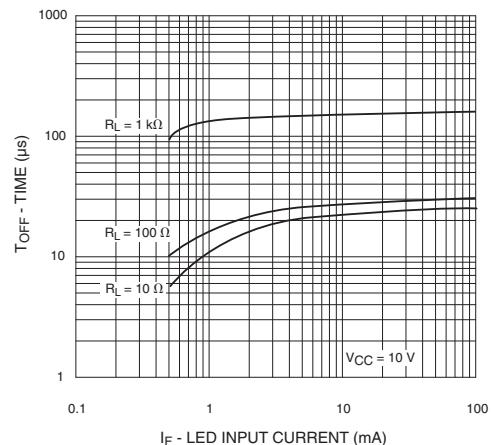


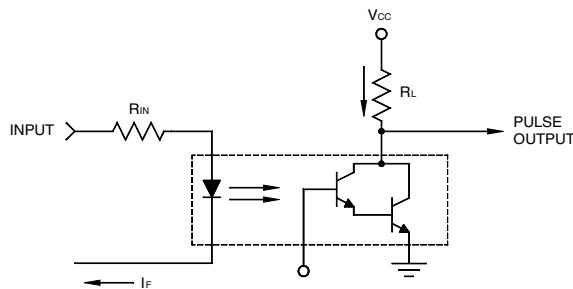
Fig. 6 Turn-Off Time vs. Input Current



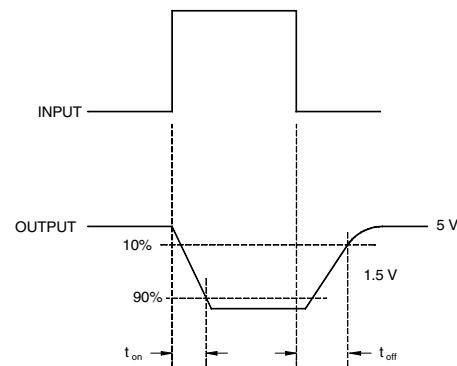
CNX48U	H11B1	H11B2	H11B255	H11B3
MOC8080	TIL113			

TYPICAL ELECTRO-OPTICAL CHARACTERISTIC CURVES

(25°C Free air temperature unless otherwise specified) (Cont.)

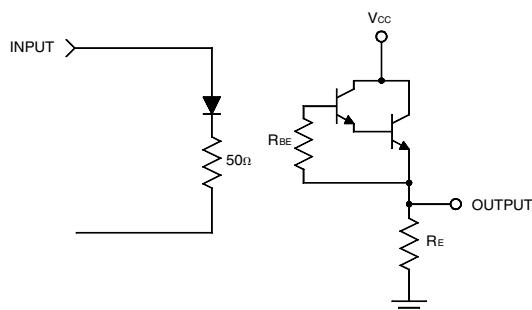


Test Circuit (All devices except CNX48U)

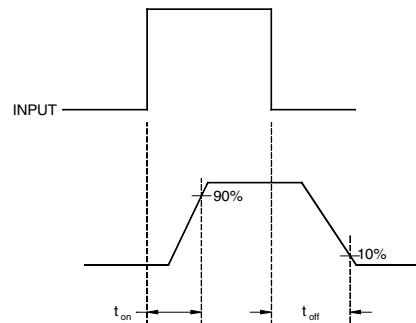


Switching Waveforms (All devices except CNX48U)

Fig. 7 Switching Time Test Circuit and Waveforms (All devices except CNX48U)



Test Circuit (CNX48U only)



Switching Waveforms (CNX48U only)

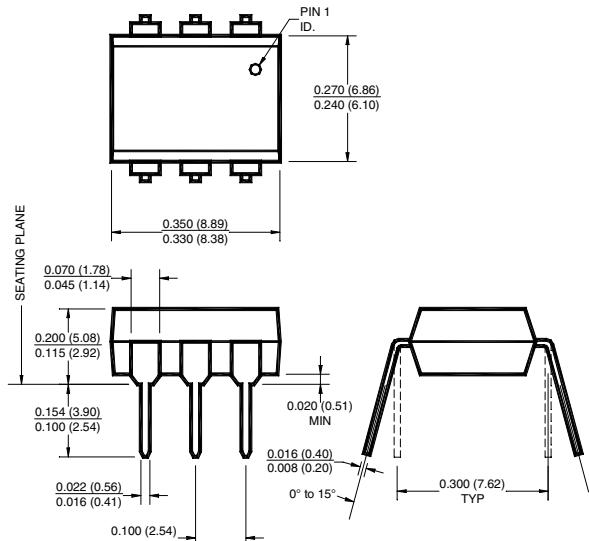
Fig. 8 Switching Time Test Circuit and Waveforms (CNX48U only)

Notes

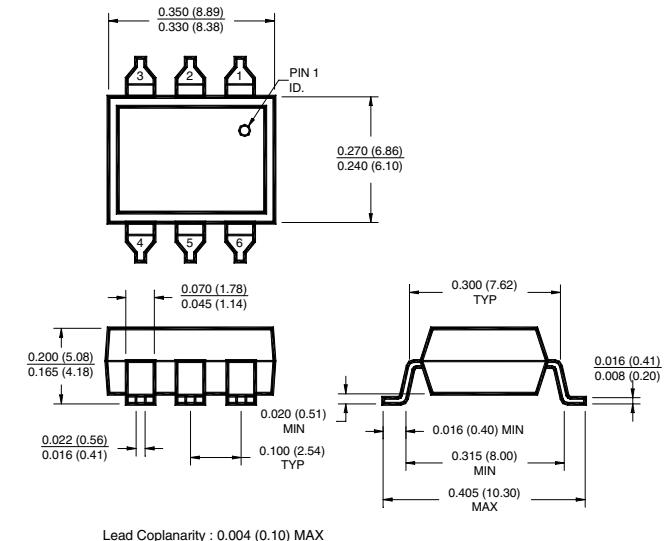
1. The current transfer ratio(I_C/I_F) is the ratio of the detector collector current to the LED input current with $V_{CE} @ 10$ V.
2. For this test, LED pins 1 and 2 are common and phototransistor pins 4,5 and 6 are common.

CNX48U H11B1 H11B2 H11B255 H11B3
MOC8080 TIL113

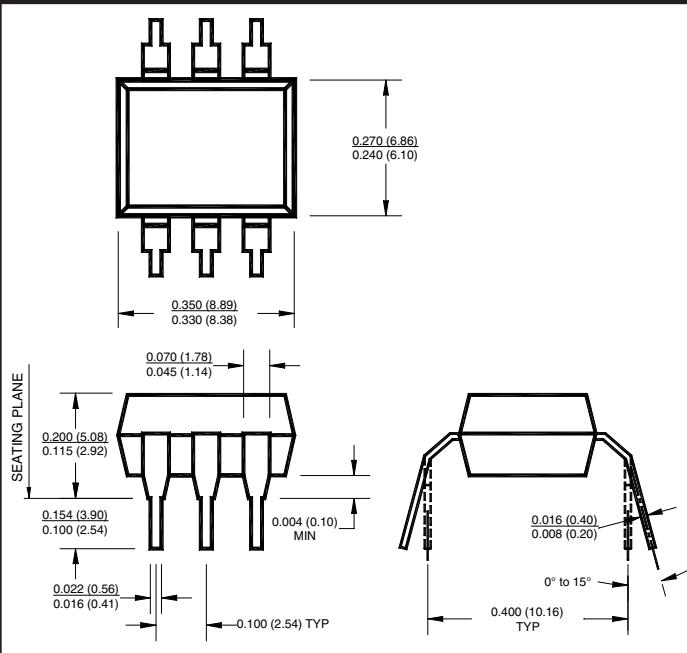
Package Dimensions (Through Hole)



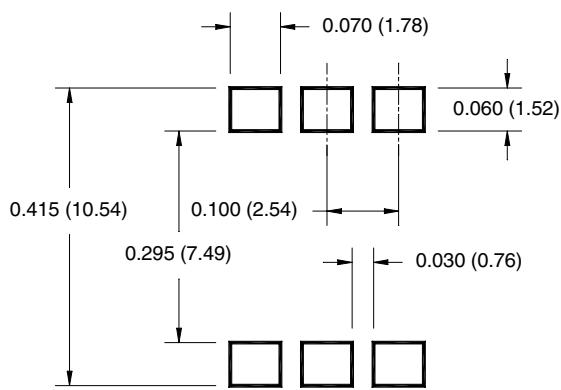
Package Dimensions (Surface Mount)



Package Dimensions (0.4"Lead Spacing)



Recommended Pad Layout for Surface Mount Leadform



NOTE

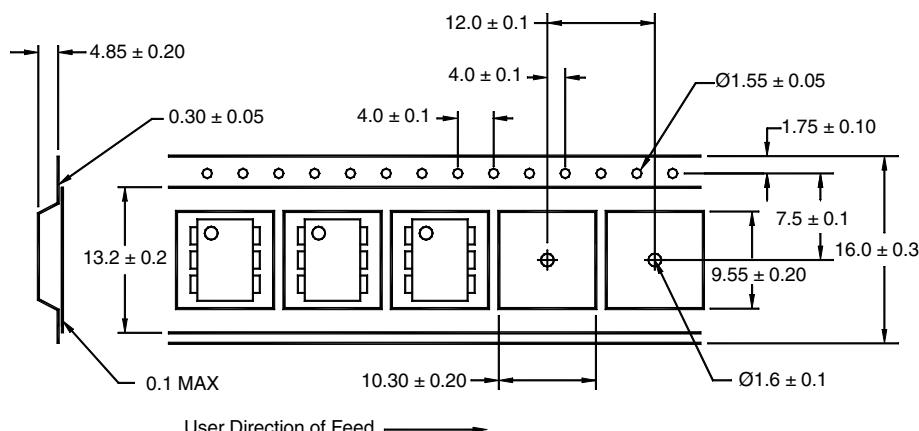
All dimensions are in inches (millimeters)

CNX48U H11B1 H11B2 H11B255 H11B3
MOC8080 TII 113

ORDERING INFORMATION

Option	Order Entry Identifier	Description
S	.S	Surface Mount Lead Bend
SD	.SD	Surface Mount; Tape and reel
W	.W	0.4" Lead Spacing
300	.300	VDE 0884
300W	.300W	VDE 0884, 0.4" Lead Spacing
3S	.3S	VDE 0884, Surface Mount
3SD	.3SD	VDE 0884, Surface Mount, Tape & Reel

QT Carrier Tape Specifications (“D” Taping Orientation)



NOTE

All dimensions are millimeters

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.